## NSN 5962-01-171-7536

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View Online at https://aerobasegroup.com/nsn/5962-01-171-7536

Body Length:
1.290 inches
Body Width:
Between 0.500 inches and 0.610 inches
Body Height:
0.210 inches
Maximum Power Dissipation Rating:
575.0 milliwatts
Operating Tempurature Range:
-55.0/+125.0 degrees celsius
Storage Tempurature Range:
-65.0/+150.0 degrees celsius
Features Provided:
Hermetically sealed and burn in and bipolar and monolithic and programmable and w/enable and w/open collector
Inclosure Material:
Ceramic
Inclosure Configuration:
Dual-in-line
Output Logic Form:
Transistor-transistor logic
Input Circuit Pattern:
8 input
Case Outline Source And Designator:
D-3 mil-m-38510
Terminal Surface Treatment:
Solder
Voltage Rating And Type Per Characteristic:
5.5 volts power source
Time Rating Per Chacteristic:
140.00 nanoseconds propagation delay time, low to high level output and 140.00 nanoseconds propagation delay time, high to low leve
output
Memory Device Type:
Rom
Test Data Document:
96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).
Terminal Type And Quantity:
24 printed circuit
Shelf Life:
N/a
Unit Of Measure:
<del></del>

Yes - demil/mli

Demilitarization:

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